

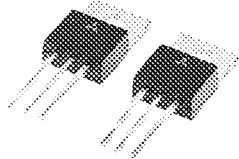
PRELIMINARY
 Notice: This is not a final specification.
 Some parametric limits are subject to change.

MITSUBISHI Pch POWER MOSFET

FX3UMJ-06

HIGH-SPEED SWITCHING USE

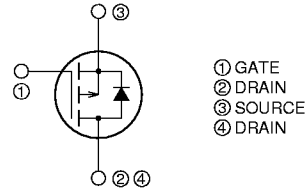
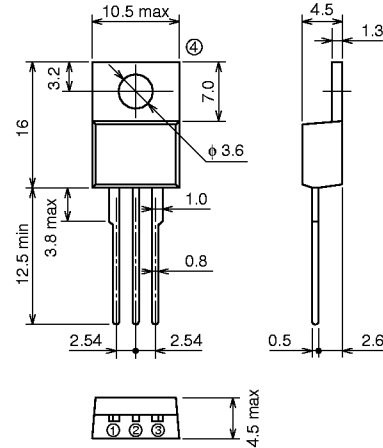
FX3UMJ-06



- 4V DRIVE
- V_{DSS} -60V
- r_{DS (ON)} (MAX) 0.46Ω
- I_D -3A
- Integrated Fast Recovery Diode (TYP.) 40ns

OUTLINE DRAWING

Dimensions in mm



TO-220

APPLICATION

Motor control, Lamp control, Solenoid control
 DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25 °C)

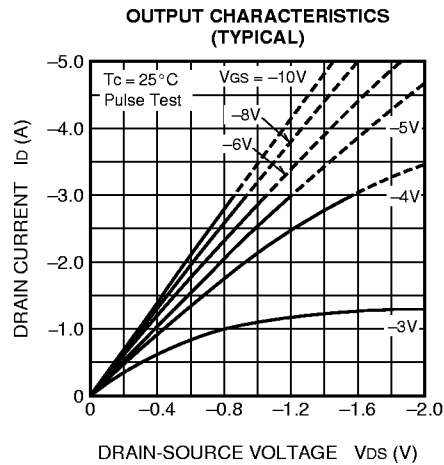
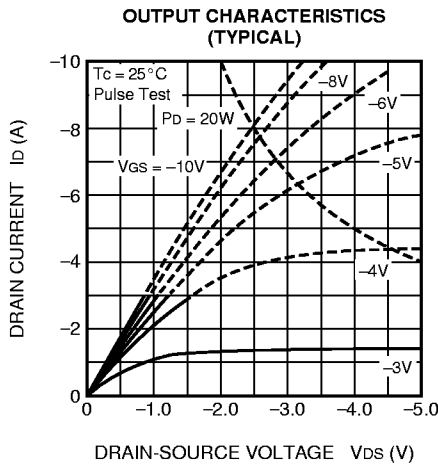
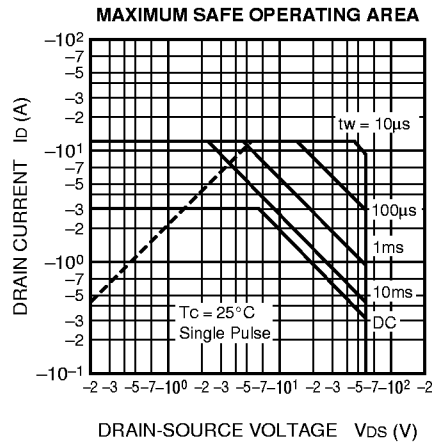
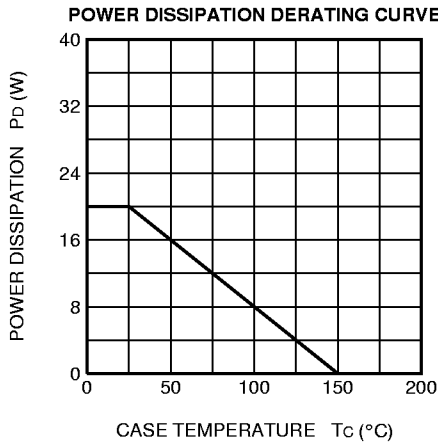
Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	-60	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±20	V
I _D	Drain current		-3	A
I _{DM}	Drain current (Pulsed)		-12	A
I _{DA}	Avalanche drain current (Pulsed)	L = 100μH	-3	A
I _S	Source current		-3	A
I _{SM}	Source current (Pulsed)		-12	A
P _D	Maximum power dissipation		20	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	2.0	g

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ELECTRICAL CHARACTERISTICS (Tch = 25°C)

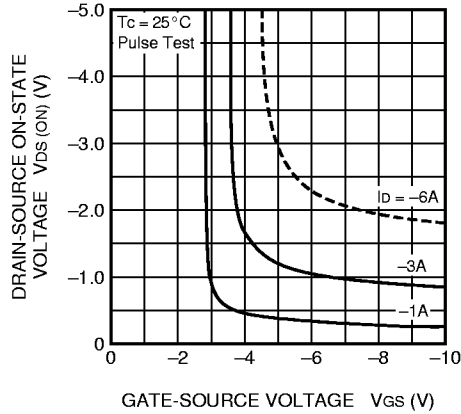
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	ID = -1mA, VGS = 0V	-60	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = -60V, VGS = 0V	—	—	-0.1	mA
VGS(th)	Gate-source threshold voltage	ID = -1mA, VDS = -10V	-1.3	-1.8	-2.3	V
rDS(ON)	Drain-source on-state resistance	ID = -1A, VGS = -10V	—	0.35	0.46	Ω
rDS(ON)	Drain-source on-state resistance	ID = -1A, VGS = -4V	—	0.57	0.80	Ω
VDS(ON)	Drain-source on-state voltage	ID = -1A, VGS = -10V	—	-0.35	-0.46	V
yfs	Forward transfer admittance	ID = -1A, VDS = -5V	—	2.0	—	S
Ciss	Input capacitance	VDS = -10V, VGS = 0V, f = 1MHz	—	520	—	pF
Coss	Output capacitance		—	104	—	pF
Crss	Reverse transfer capacitance		—	31	—	pF
td(on)	Turn-on delay time	VDD = -30V, ID = -1A, VGS = -10V, RGEN = RGS = 50Ω	—	8	—	ns
tr	Rise time		—	5	—	ns
td(off)	Turn-off delay time		—	35	—	ns
tf	Fall time		—	15	—	ns
VSD	Source-drain voltage	IS = -1A, VGS = 0V	—	-1.0	-1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	6.25	°C/W
trr	Reverse recovery time	IS = -3A, dis/dt = 100A/μs	—	40	—	ns

PERFORMANCE CURVES

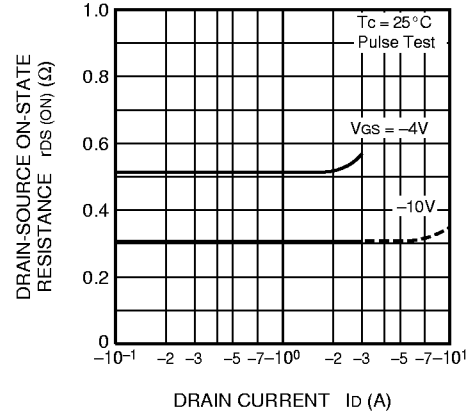


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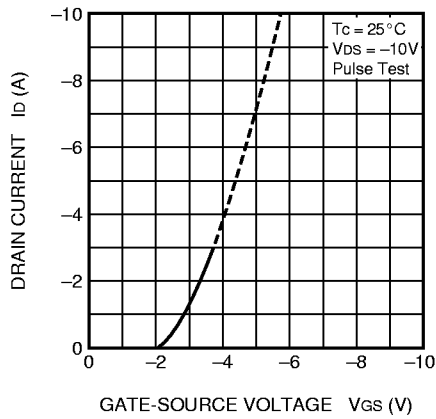
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



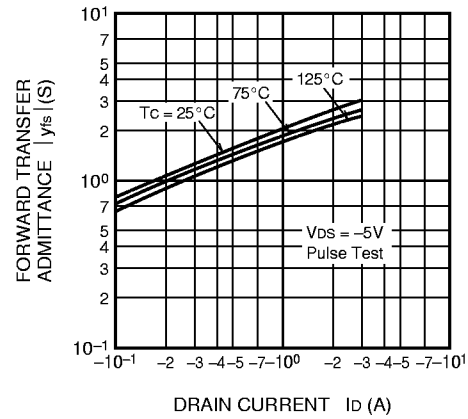
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



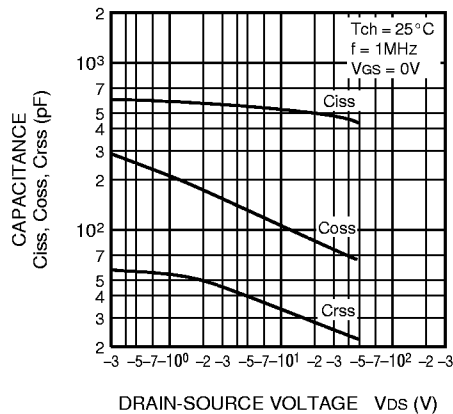
TRANSFER CHARACTERISTICS (TYPICAL)



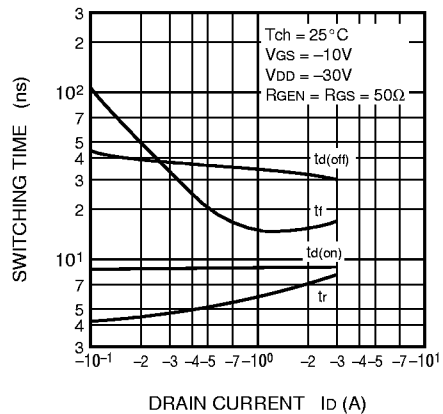
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)

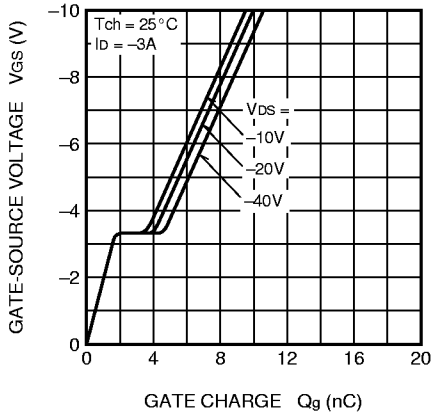


SWITCHING CHARACTERISTICS (TYPICAL)

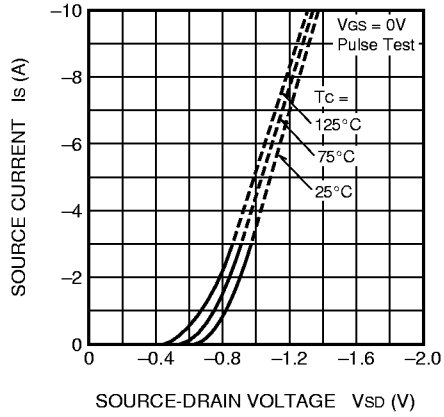


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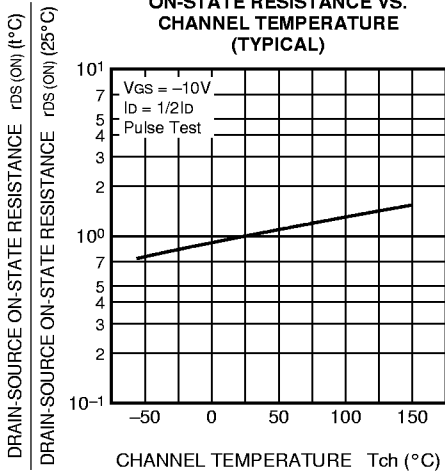
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



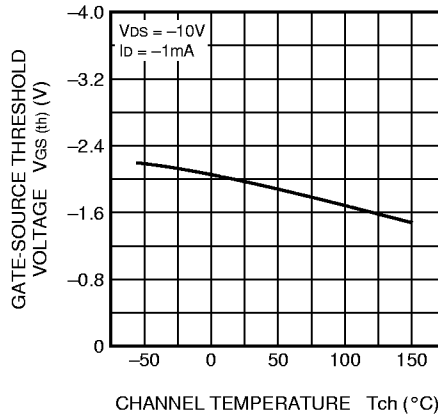
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



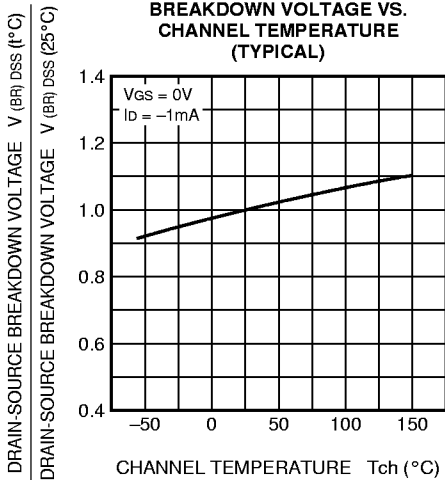
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

